

N-Channel MOSFETs (>500V...900V); Package: PG-TO252-3; VDS (max): 600.0 V;
 Package: DPAK (TO-252); RDS(ON) @ TJ=25°C VGS=10: 380.0 mOhm; ID(max) @
 TC=25°C: 10.6 A; IDpuls (max): 30.0 A;

Manufacturers	<u>Infineon Technologies Corporation</u>
Package/Case	TO-252
Product Type	Transistors
RoHS	Rohs
Lifecycle	



Images are for reference only

Please submit RFQ for IPD60R380C6 or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

General Description

IPD60R380C6 is a specific model of a power MOSFET (Metal-Oxide-Semiconductor Field-Effect Transistor) developed by Infineon Technologies. Here are some details about this MOSFET:

Features

It is a N-channel enhancement mode MOSFET.

It has a maximum drain-source voltage of 600V.

It has a maximum continuous drain current of 60A.

It has a low on-resistance of 0.038 ohms at 25°C.

It has a fast switching speed.

Application

It is used in various power electronics applications such as DC-DC converters, motor control, uninterruptible power supplies (UPS), and switching power supplies.



Related Products



[IPP60R070CFD7](#)

Infineon Technologies Corporation
TO-220-3



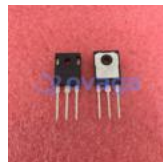
[IPB180N06S4-H1](#)

Infineon Technologies Corporation
PG-TO263-7-3



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